Masatoshi Tanaka

List of Publications by Year
in descending order

61	390	840776 11	888059 17
papers	citations	h-index	g-index

61	61	61	491
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Thermal oxidation process on Si(113)-(3 Ã— 2) investigated using high-temperature scanning tunneling microscopy. Beilstein Journal of Nanotechnology, 2022, 13, 172-181.	2.8	0
2	Multiple-peak resonance of optical second harmonic generation arising from band nesting in monolayer transition metal dichalcogenides <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>T</mml:mi><mml:msub><mml:mi>X</mml:mi><mml:mn> on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Si</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:mo>/</mml:mo><mml:mi>Si</mml:mi><mml:m.	3.2	12
3	Second-harmonic generation from supported carbon nanotube films grown by chemical vapor deposition on fused silica. Japanese Journal of Applied Physics, 2019, 58, 032006.	1.5	1
4	Electronic structure of Î±-sexithiophene ultrathin films grown on. Physical Chemistry Chemical Physics, 2018, 20, 1114-1126.	2.8	8
5	Deposition of ZrON thin films by reactive magnetron sputtering using a hollow cylindrical target. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	6
6	Observation of the adsorption and desorption kinetics of weakly bound CO on Si(001)-c(4Ã—2) by means of reflectance difference spectroscopy. Surface Science, 2017, 662, 82-86.	1.9	1
7	Photoinduced charge transfer from vacuum-deposited molecules to single-layer transition metal dichalcogenides. Japanese Journal of Applied Physics, 2016, 55, 065201.	1.5	13
8	Characterization of Effective Mobility and Its Degradation Mechanism in MoS2MOSFETs. IEEE Nanotechnology Magazine, 2016, 15, 651-656.	2.0	14
9	Phonon Properties of Few-Layer Crystals of Quasi-One-Dimensional ZrS₃ and ZrSe₃. Journal of Physical Chemistry C, 2016, 120, 4653-4659.	3.1	41
10	Time-resolved chemiluminescence of firefly luciferin generated by dissolving oxygen in deoxygenated dimethyl sulfoxide containing potassium <i>tert</i>-butoxide. Biophysics and Physicobiology, 2015, 12, 69-78.	1.0	0
11	Characterization of effective mobility by split C-V technique in MoS2 MOSFETs with high-k/metal gate. , 2015, , .		0
12	Adsorption and self-assembled structures of sexithiophene on the Si(111)-3Ã—3-Ag surface. Journal of Chemical Physics, 2015, 142, 204701.	3.0	6
13	Ultrathin GeSn p-channel MOSFETs grown directly on Si(111) substrate using solid phase epitaxy. Japanese Journal of Applied Physics, 2015, 54, 04DA07.	1.5	14
14	Molecular Motion Induced by Multivibronic Excitation on Semiconductor Surface. Journal of Physical Chemistry C, 2014, 118, 1554-1559.	3.1	5
15	Decay Processes of Si 2sCore Holes in Si(111)-7 Ã— 7 Revealed by Si Auger Electron Si 2sPhotoelectron Coincidence Measurements. Journal of the Physical Society of Japan, 2014, 83, 094704.	1.6	2
16	Real-Time Analysis of Initial Oxidation Process on Si(001) by Means of Surface Differential Reflectance Spectroscopy and Reflectance Difference Spectroscopy. Springer Series in Optical Sciences, 2014, , 29-44.	0.7	0
17	Site-specific ion desorption from condensed F3SiCD2CH2Si(CH3)3 induced by Si-2p core-level ionizations studied with photoelectron photoion coincidence (PEPICO) spectroscopy, Auger photoelectron coincidence spectroscopy (APECS) and Auger electron photoion coincidence (AEPICO) spectroscopy. Surface Science, 2013, 607, 174-180.	1.9	5
18	SHG enhancement by roughness-induced surface plasmon excitation in alkali-metal overlayers grown on Si(111)-7Ã—7. Applied Surface Science, 2013, 267, 58-61.	6.1	2

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19	Characterization of Monolayer Oxide Formation Processes on High-Index Si Surfaces by Photoelectron Spectroscopy with Synchrotron Radiation. Applied Physics Express, 2013, 6, 115701.	2.4	5
20	Oxynitride Formation Processes on Si(001) Studied by Means of Reflectance Difference Spectroscopy. Japanese Journal of Applied Physics, 2013, 52, 126505.	1.5	2
21	Time Courses and Timeâ€Resolved Spectra of Firefly Bioluminescence Initiated by Two Methods of <scp>ATP</scp> Injection and Photolysis of Caged <scp>ATP</scp>. Photochemistry and Photobiology, 2013, 89, 1490-1496.	2.5	5
22	Tensile-Strained GeSn Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Devices on Si(111) Using Solid Phase Epitaxy. Applied Physics Express, 2013, 6, 101301.	2.4	40
23	Attempts to Improve the Sensitivity and the Energy Resolution of an Analyzer for Auger Photoelectron Coincidence Spectroscopy and Electron Ion Coincidence Spectroscopy. Journal of the Vacuum Society of Japan, 2013, 56, 507-510.	0.3	0
24	2PT186 Time Dependent Characteristics of Firefly Bioluminescence Initiated by Two Methods with Usual ATP Injection and Photolysis of Caged-ATP(The 50th Annual Meeting of the Biophysical Society of) Tj ETQq0 0 0 rgBT /Overlock 10	0.0	0
25	Time-evolution of thermal oxidation on high-index silicon surfaces: Real-time photoemission spectroscopic study with synchrotron radiation. Surface Science, 2012, 606, 1685-1692.	1.9	9
26	Study of Local Valence Electronic States of SiO2Ultrathin Films Grown on Si(111) by Using Auger Photoelectron Coincidence Spectroscopy: Upward Shift of Valence-Band Maximum Depending on the Interface Structure. Journal of the Physical Society of Japan, 2012, 81, 074706.	1.6	4
27	Simple Low-Outgassing Atomic Hydrogen Source. Journal of the Vacuum Society of Japan, 2012, 55, 403-404.	0.3	1
28	Surface-site-selective study of valence electronic states of a clean Si(111)-7Ã—7 surface using SiL23VVAuger electron and Si 2pphotoelectron coincidence measurements. Physical Review B, 2011, 83, .	3.2	12
29	Auger electron spectra of hydrogenated Si(111)-1Ã—1 surface obtained fromSi-L₂₃VVAuger electron Si-2pphotoelectron coincidence measurements. Journal of Physics: Conference Series, 2011, 288, 012016.	0.4	0
30	Local Valence Electronic States of SiO2 Ultrathin Films Grown on Si(100) Studied Using Auger Photoelectron Coincidence Spectroscopy: Observation of Upward Shift of Valence-Band Maximum as a Function of SiO2 Thickness. Journal of the Physical Society of Japan, 2011, 80, 084703.	1.6	3
31	The Reaction Process of Firefly Bioluminescence Triggered by Photolysis of Caged-ATP. Photochemistry and Photobiology, 2011, 87, 653-658.	2.5	4
32	On the resonant SHG response of ultra-thin alkali (K, Rb)-covered Si(111)-7Ã—7. Applied Surface Science, 2011, 257, 3758-3762.	6.1	2
33	Vacuum-ultraviolet reflectance difference spectroscopy for characterizing dielectricsâ€“semiconductor interfaces. Thin Solid Films, 2011, 519, 2830-2833.	1.8	2
34	SiO2/Si interfaces on high-index surfaces: Re-evaluation of trap densities and characterization of bonding structures. Applied Physics Letters, 2011, 98, 092906.	3.3	14
35	Contribution in Semiconductor Industry of Surface Science -Clusters Observed for Adsorbate Coverages Close to the Saturation Coverage-. Hyomen Kagaku, 2011, 32, 302-307.	0.0	3
36	Real-time Optical Measurement of Alkali-metal Adsorption and Desorption Processes on a Si(001) Surface. Journal of the Vacuum Society of Japan, 2011, 54, 220-223.	0.3	0

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37	Surface-Site-Selective Study of Valence Electronic Structures of Clean Si(100)-2Ã—1 Using Si-L23VV Auger Electronâ€“Si-2p Photoelectron Coincidence Spectroscopy. Journal of the Physical Society of Japan, 2010, 79, 064714.	1.6	8
38	1P269 Time dependence of firefly bioluminescence induced by the photoresolution of caged-ATP(Photobiology:Vision & Photoreception,The 48th Annual Meeting of the Biophysical) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5		0
39	Topmost-surface-sensitive Si-2p photoelectron spectra of clean Si(100)-2Ã—1 measured with photoelectron Auger coincidence spectroscopy. Surface Science, 2010, 604, L27-L30.	1.9	8
40	Reaction Kinetics in the Rapid Oxide Growth on Si(001)-(2Ã—1) Probed with Reflectance Difference Spectroscopy. Japanese Journal of Applied Physics, 2010, 49, 055702.	1.5	7
41	Reflectance Difference Spectroscopy in Vacuumâ€“Ultraviolet Range: Developing Measurement System and Applying to Characterization of SiO2/Si Interfaces. Japanese Journal of Applied Physics, 2010, 49, 022403.	1.5	5
42	Theoretical Investigation of the Reaction Pathway of O Atom on Si(001)-(2 Ã— 1). Journal of Physical Chemistry C, 2010, 114, 15671-15677.	3.1	11
43	Real-time Analysis of Initial Oxidation Process on Si(001) by Means of Surface Differential Reflectance Spectroscopy and Reflectance Difference Spectroscopy. Journal of the Vacuum Society of Japan, 2010, 53, 413-420.	0.3	1
44	Construction and Evaluation of a Miniature Electron Ion Coincidence Analyzer Mounted on a Conflat Flange with an Outer Diameter of 114 mm. Analytical Sciences, 2008, 24, 87-92.	1.6	4
45	Development of an Apparatus for High-Resolution Auger Photoelectron Coincidence Spectroscopy (APECS) and Electron Ion Coincidence (EICO) Spectroscopy. Journal of the Vacuum Society of Japan, 2008, 51, 749-757.	0.3	14
46	TIME-RESOLVED MEASUREMENT OF FIREFLY BIOLUMINESCENCE USING PHOTOLYSIS OF CAGED-ATP. , 2007, , .		0
47	K-induced surface structural change of Si(111)-7Ã—7 probed by second-harmonic generation. Applied Surface Science, 2006, 252, 5296-5299.	6.1	1
48	Photon-stimulated desorption from chlorinated Si(111): Etching of SiCl by picosecond-pulsed laser irradiation. Physical Review B, 2006, 73, .	3.2	7
49	Recent progress in coincidence studies on ion desorption induced by core excitation. Journal of Physics Condensed Matter, 2006, 18, S1389-S1408.	1.8	12
50	Study of Si(111) Surface Reflection Spectrum by Cluster Calculation. Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 138-140.	0.2	2
51	Formation Process of Poly-bromides in Br Adsorption on Si(111) Surface. Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 144-146.	0.2	0
52	Dependence of Surface Differential Reflectance Spectra on the Incident Photon Energy during Initial Oxidation on Si(001). Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 323-326.	0.2	2
53	Desorption Induced by Excited Electrons from Semiconductor Surfaces (I)-Desorption Induced by Electron-/hole-injection into Halogen-adsorbed Silicon Surfaces-. Shinku/Journal of the Vacuum Society of Japan, 2006, 49, 600-604.	0.2	0
54	Surface modification of Cl-adsorbed Si(111)-7Ã—7 by the irradiation of infrared pulsed laser. Surface Science, 2004, 566-568, 1137-1142.	1.9	2

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55	Isothermal desorption process of Cl-covered Si(111) studied by surface differential reflectivity spectroscopy. Surface Science, 2003, 527, 21-29.	1.9	8
56	Thermal Desorption Process of Bromide on Si(111) Studied by Highly Sensitive Mass Spectroscopy. Japanese Journal of Applied Physics, 2003, 42, 593-596.	1.5	11
57	Temporally Resolved Spectroscopy of Laser Ablation of NiO.. Shinku/Journal of the Vacuum Society of Japan, 1998, 41, 262-265.	0.2	0
58	Optical spectra near the band edge ofZrS3andZrSe3. Physical Review B, 1993, 48, 1356-1360.	3.2	10
59	Uniaxial Stress-Effect on the One-Dimensional Band Structure of [Pt (en)2][Pt (en)2Cl2](ClO4)4(en=ethylenediamine). Journal of the Physical Society of Japan, 1987, 56, 1197-1202.	1.6	11
60	Raflectance Spectra and Band Structures of Quasi-One-Dimensional [Pt(en)2][Pt(en)2X2](ClO4)4(X=I) Tj ETQq0 0 0 rgBT /Overlock 10	1.6	25
61	Conduction Band Structure Determined from the g-Values of the Excitons in VI B Transition Metal Dichalcogenides. Journal of the Physical Society of Japan, 1982, 51, 3888-3892.	1.6	5